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November 2013

FQD8P10 / FQU8P10

P-Channel QFET® MOSFET

-100 V, -6.6 A, 530 $m\Omega$

Description

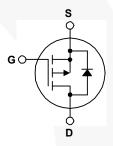
This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- -6.6 A, -100 V, R_{DS(on)} = 530 m Ω (Max) @ V_{GS} = -10 V, I_D = -3.3 A
- Low Gate Charge (Typ. 12 nC)
- Low Crss (Typ. 30 pF)
- 100% Avalanche Tested







Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQD8P10TM / FQU8P10TU	Unit
V_{DSS}	Drain-Source Voltage		-100	V
I _D	Drain Current - Continuous (T _C = 25	5°C)	-6.6	Α
	- Continuous (T _C = 10	00°C)	-4.2	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	-26.4	Α
V _{GSS}	Gate-Source Voltage		± 30	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	150	mJ
I _{AR}	Avalanche Current	(Note 1)	-6.6	A
E _{AR}	Repetitive Avalanche Energy	(Note 1)	4.4	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-6.0	V/ns
P_{D}	Power Dissipation (T _A = 25°C) *		2.5	W
	Power Dissipation (T _C = 25°C)		44	W
	- Derate above 25°C		0.35	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	FQD8P10TM FQU8P10TU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max. 2.84		
В	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	50	1

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQD8P10TM	FQD8P10	D-PAK	Tape and Reel	330 mm	16 mm	2500 units
FQU8P10TU	FQU8P10	I-PAK	Tube	N/A	N/A	70 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Uni
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-100			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		-0.1		V/°(
I _{DSS}	Zana Cata Valtana Dunin Comment	V _{DS} = -100 V, V _{GS} = 0 V			-1	μА
	Zero Gate Voltage Drain Current	V _{DS} = -80 V, T _C = 125°C			-10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
On Cha	aracteristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-2.0		-4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = -10 V, I _D = -3.3 A		0.41	0.53	Ω
g _{FS}	Forward Transconductance	V _{DS} = -40 V, I _D = -3.3 A		4.1		S
	ic Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$		360	470	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		120	155	pF
C _{rss}	Reverse Transfer Capacitance			30	40	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = -50 V, I _D = -8.0 A,		11	30	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		110	230	ns
$t_{d(off)}$	Turn-Off Delay Time			20	50	ns
t _f	Turn-Off Fall Time	(Note 4)		35	80	ns
Qg	Total Gate Charge	$V_{DS} = -80 \text{ V}, I_{D} = -8.0 \text{ A},$	/	12	15	nC
Q _{gs}	Gate-Source Charge	V _{GS} = -10 V		3.0	-	nC
Q _{gd}	Gate-Drain Charge	(Note 4)		6.4		nC
Drain-S	Source Diode Characteristics a	nd Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				-6.6	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				-26.4	Α
	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = -6.6 A			-4.0	V
V_{SD}						
V _{SD}	Reverse Recovery Time	$V_{GS} = 0 \text{ V}, I_{S} = -8.0 \text{ A},$		98		ns

- **Notes:**1. Repetitive rating : pulse-width limited by maximum junction temperature.
 2. L = 5.2 mH, I_{AS} = -6.6 A, V_{DD} = -25 V, R_{O} = 25 Ω , starting T_{J} = 25°C.
 3. I_{SD} ≤ -8.0 A, di/dt ≤ 300 A/ μ s, V_{DD} ≤ BV $_{DSS}$, starting T_{J} = 25°C.
 4. Essentially independent of operating temperature.

Typical Characteristics

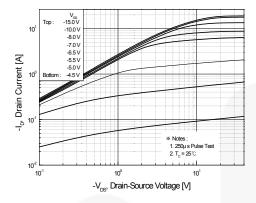


Figure 1. On-Region Characteristics

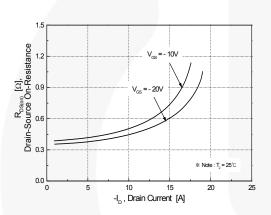


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

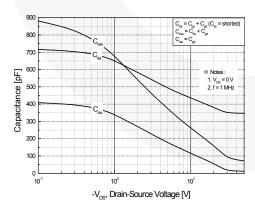


Figure 5. Capacitance Characteristics

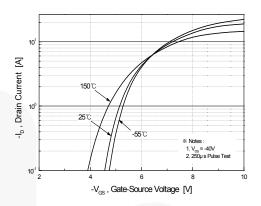


Figure 2. Transfer Characteristics

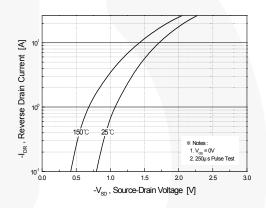


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

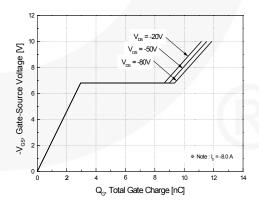
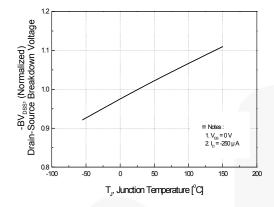


Figure 6. Gate Charge Characteristics

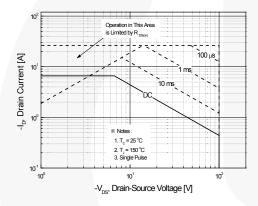
Typical Characteristics (Continued)



3.0

Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



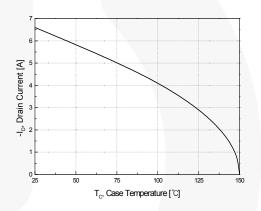


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

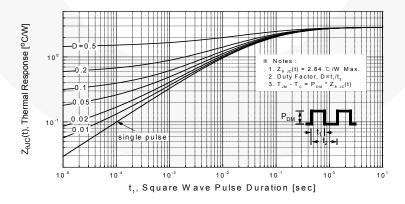


Figure 11. Transient Thermal Response Curve

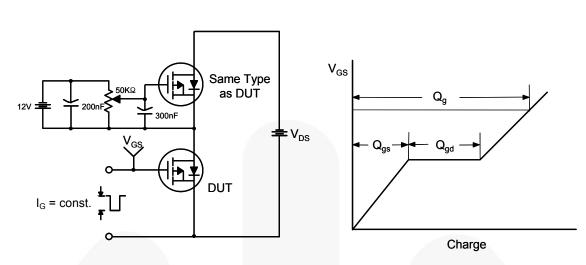


Figure 12. Gate Charge Test Circuit & Waveform

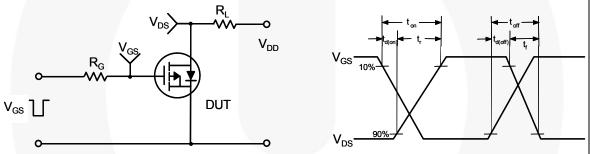


Figure 13. Resistive Switching Test Circuit & Waveforms

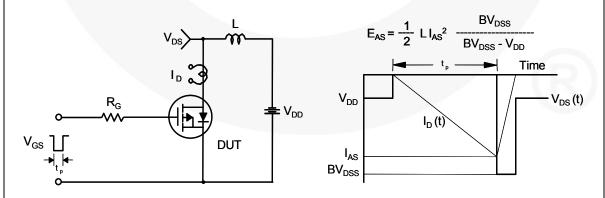
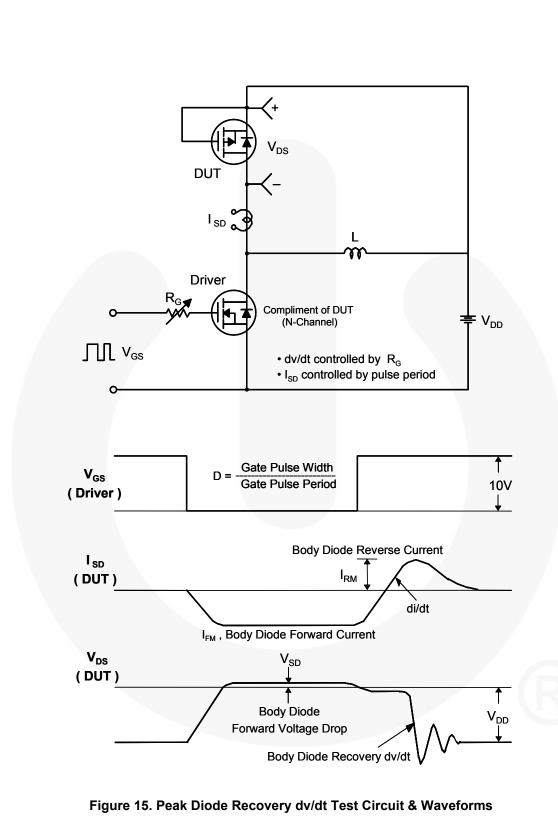


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Mechanical Dimensions

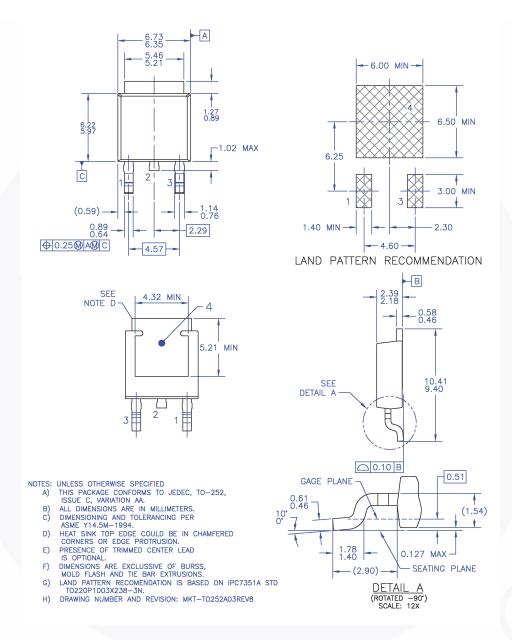


Figure 16. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

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Mechanical Dimensions

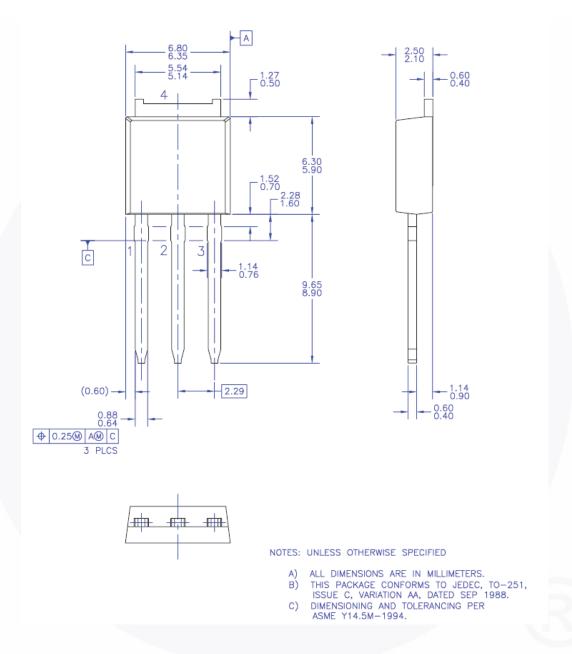


Figure 17. TO251 (I-PAK), Molded, 3-Lead

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